Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	211514	(nitrogen or "N.sub.2") with (oxygen or "O.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:13
L2	624	(nitrogen or "N.sub.2") with (oxygen or "O.sub.2") with ("CF.sub.4" or tetra$1fluoride) with (hydrogen or "H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:14
L3	95	2 same (resist or photo$1resist or photo$1sensitive)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:15
L4	93	3 and @ay<="2003"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:15
L5	77	4 and (ratio or sccm)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 14:15
L6	2	Hsu-Li-Te.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:50
L7	3	Chen-Chia-Lun.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:50
L8	13	Peng-chiang-Jen.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:51

L9	15	6 or 7 or 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:51
S30 6	4228	memory and ((polysilicon or (poly$1crystalline adj silicon)) with spacer)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/25 09:16
S30 7	4145	S306 and (gate or electrode)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:07
S30 8	3539	S307 and (source and drain)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:07
S30 9	3380	S308 and (etch or etching)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:08
S31 0	812	S309 and tunneling	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:08
S31 1	555	S310 and non$1volatile	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:11
S31 2	440	S311 and @ay<="2002"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S31 3	420	S312 and (mask or resist or photo$1resist or photo$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S31 4	420	S313 and gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S31 5	387	S313 and (dope or doping or dopant or implant$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:10
S31 6	368	S315 and (non$1volatile near3 memory)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/19 18:11
S31 7	7803	(oxygen or "O.sub.2") with (hydrogen or "H.sub.2") with (fluorine or "CF.sub.4" or fluoro$1carbon)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 13:57
S31 8	1723	S317 and (resist or photo$1resist or photo$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/20 18:21
S31 9	341	S318 and (source same drain)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/20 18:21

S32 0	247	S319 and (nitrogen or "N.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/20 18:22
S32 1	225	S320 and (implant or implanting or implanted or implantation or dope or doping or dopant or doped)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 13:58
S32 2	196	S321 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/20 18:23
S32 3	7815	(oxygen or "O.sub.2") with (hydrogen or "H.sub.2") with (fluorine or "CF.sub.4" or fluoro$1carbon)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/22 15:01
S32 4	450	S323 same (resist or photo$1resist or photo$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 13:58
S32 5	422	S324 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 13:58
S32 6	285	S325 and (implant or implanting or implanted or implantation or dope or doping or dopant or doped)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 13:59
S32 7	100	S326 and source and drain	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 13:59
S32 8	5	("5401998" | "5786262" | "5795801" | "5851900" | "5960276").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:13
S32 9	89373	CMO	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:13
S33 0	9160	CMOS and spacer and (dope or doping or dopant or implant$3 or implantation)	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 17:19
S33 1	4323	S330 and ((resist or photo$1resist or photo$1sensitive) same (dope or doping or dopant or implant$3 or implantation))	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:15
S33 2	4115	S331 and source and drain	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:15
S33 3	3857	S332 and @ay<="2003"	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:15
S33 4	2873	S333 and ((polysilicon or (poly$1crystalline adj silicon)) with (gate or electrode))	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:17

S33 5	326	S334 and ((oxygen or "O.sub.2") with (hydrogen or "H.sub.2"))	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 17:23
S33 6	316	S335 not S327	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:17
S33 7	272	S336 and plasma	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 15:19
S33 8	7	("5290720" | "6156598" | "6251764" | "6277683" | "6319783" | "6346468" | "6348387").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 16:28
S33 9	932	S330 and ((dope or doping or dopant or implant$3 or implantation) with (amorphiz$3 or amorphous or saturat$3 or un$1saturat$3))	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 18:13
S34 0	853	S339 and source and drain	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 17:23
S34 1	853	S340 and spacer	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 17:23
S34 2	129	S340 and ((oxygen or "O.sub.2") with (hydrogen or "H.sub.2"))	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 17:24
S34 3	119	S342 and @ay<="2003"	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 17:24
S34 4	11	("4800170" | "4992137" | "5607884" | "5641380" | "5656546" | "5731239" | "5863820" | "5866451" | "5869359" | "6025273" | "6030898").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 18:05
S34 5	167	S330 and ((dope or doping or dopant or implant$3 or implantation) with (saturat$3 or un$1saturat$3 or bond))	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 18:14
S34 6	157	S345 and @ay<="2003"	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 18:14
S34 7	151	S346 and gate	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/21 18:14

S34 8	3776	(oxygen or "O.sub.2") with (hydrogen or "H.sub.2") with (fluorine or "CF.sub.4" or fluoro$1carbon) with (nitrogen or "N.sub.2")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/22 15:02
S34 9	159	S348 same (resist or photo$1resist or photo$1sensitive)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/22 15:22
S35 0	151	S349 and @ay<="2003"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/22 15:22